#### S/N Unknown

#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Paul A. Farrar et al.

Examiner: Unknown

Serial No.:

Unknown

Group Art Unit: Unknown

Filed:

Herewith

Docket: 303.469US3

Title:

THERMAL PROCESSING OF METAL ALLOYS FOR AN IMPROVED CMP

PROCESS IN INTEGRATED CIRCUIT FABRICATION

### **PRELIMINARY AMENDMENT**

Commissioner for Patents Washington, D.C. 20231

When the above-identified patent application is taken up for consideration, please amend the application as follows:

# **IN THE SPECIFICATION**

On page 1, please add the following new paragraph under the title:

--This application is a Continuation of U.S. Application No. 09/038,252, filed on March

10, 1998.-

## IN THE CLAIMS

Please cancel claims 1-17 after adding the following new claims.

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20. A memory device comprising:

an array of memory cells;

internal circuitry; and

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metal contacts and interconnects coupled to the memory cells and internal circuitry, wherein the metal contacts and interconnects are formed by annealing the memory at a temperature sufficient to drive alloy dopants into solid solution prior to polishing the memory device to remove portions of a metal layer and form the metal contacts and interconnects.

21. The memory device of claim 20 wherein the memory device is annealed following pollshing of the memory device to increase the conductivity of the metal contacts and interconnects.